

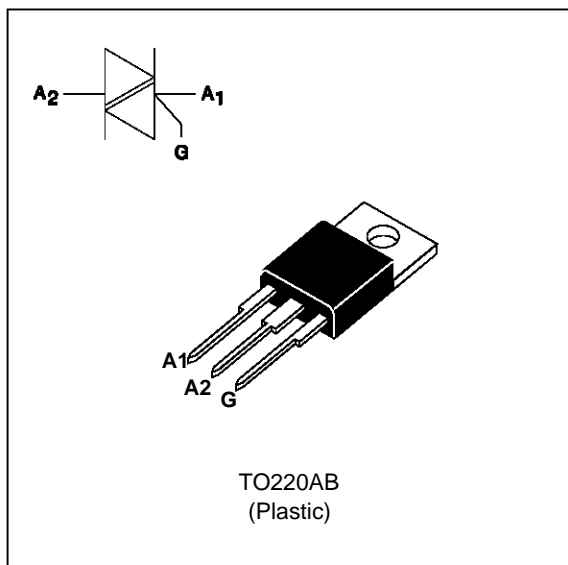
SENSITIVE GATE TRIACS

FEATURES

- VERY LOW $I_{GT} = 10\text{mA}$ max
- LOW $I_H = 15\text{mA}$ max
- BTA Family :
INSULATING VOLTAGE = $2500V_{(RMS)}$
(UL RECOGNIZED : E81734)

DESCRIPTION

The BTA/BTB06 T/D/S/A triac family are high performance glass passivated PNP devices. These parts are suitable for general purpose applications where gate high sensitivity is required. Application on 4Q such as phase control and static switching.



ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter | | | Value | Unit |
|------------------------------------|--|-----|-------------------------|--------------------------------|------------------|
| I _{T(RMS)} | RMS on-state current (360° conduction angle) | BTA | T _c = 85°C | 6 | A |
| | | BTB | T _c = 90°C | | |
| I _{TSM} | Non repetitive surge peak on-state current (T _j initial = 25°C) | | tp = 8.3 ms | 63 | A |
| | | | tp = 10 ms | 60 | |
| I ² _t | I ² _t value | | tp = 10 ms | 18 | A ² s |
| di/dt | Critical rate of rise of on-state current Gate supply : I _G = 50mA di _G /dt = 0.1A/μs | | Repetitive F = 50 Hz | 10 | A/μs |
| | | | Non Repetitive | 50 | |
| T _{stg} T _j | Storage and operating junction temperature range | | | - 40 to + 150 - 40 to + 110 | °C °C |
| T _l | Maximum lead temperature for soldering during 10 s at 4.5 mm from case | | | 260 | °C |

| Symbol | Parameter | BTA / BTB06- | | | Unit |
|------------------------|--|--------------|-------------|-------------|------|
| | | 400 T/D/S/A | 600 T/D/S/A | 700 T/D/S/A | |
| V_{DRM} V_{RRM} | Repetitive peak off-state voltage $T_j = 110^\circ\text{C}$ | 400 | 600 | 700 | V |

THERMAL RESISTANCES

| Symbol | Parameter | | Value | Unit |
|--------------|---|-----|-------|------|
| Rth (j-a) | Junction to ambient | | 60 | °C/W |
| Rth (j-c) DC | Junction to case for DC | BTA | 4.4 | °C/W |
| | | BTB | 3.2 | |
| Rth (j-c) AC | Junction to case for 360° conduction angle (F= 50 Hz) | BTA | 3.3 | °C/W |
| | | BTB | 2.4 | |

GATE CHARACTERISTICS (maximum values)

P_G (AV) = 1W P_{GM} = 10W (tp = 20 μs) I_{GM} = 4A (tp = 20 μs) V_{GM} = 16V (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

| Symbol | Test Conditions | | Quadrant | | Suffix | | | | Unit |
|--------------------------------------|---|-----------------------|-------------|------|--------|----|----|----|------|
| | | | | | T | D | S | A | |
| I _{GT} | V _D =12V (DC) R _L =33Ω | T _j =25°C | I-II-III | MAX | 5 | 5 | 10 | 10 | mA |
| | | | IV | MAX | 5 | 10 | 10 | 25 | |
| V _{GT} | V _D =12V (DC) R _L =33Ω | T _j =25°C | I-II-III-IV | MAX | 1.5 | | | | V |
| V _{GD} | V _D =V _{DRM} R _L =3.3kΩ | T _j =110°C | I-II-III-IV | MIN | 0.2 | | | | V |
| tgt | V _D =V _{DRM} I _G = 40mA dI _G /dt = 0.5A/μs | T _j =25°C | I-II-III-IV | TYP | 2 | | | | μs |
| I _L | I _G = 1.2 I _{GT} | T _j =25°C | I-III-IV | TYP | 10 | 10 | 20 | 20 | mA |
| | | | II | | 20 | 20 | 40 | 40 | |
| I _H * | I _T = 100mA gate open | T _j =25°C | | MAX | 15 | 15 | 25 | 25 | mA |
| V _{TM} * | I _{TM} = 8.5A tp= 380μs | T _j =25°C | | MAX | 1.65 | | | | V |
| I _{DRM} I _{RRM} | V _{DRM} Rated V _{RRM} Rated | T _j =25°C | | MAX | 0.01 | | | | mA |
| | | T _j =110°C | MAX | 0.75 | | | | | |
| dV/dt * | Linear slope up to V _D =67%V _{DRM} gate open | T _j =110°C | | TYP | 10 | 10 | - | - | V/μs |
| | | | | MIN | - | - | 10 | 10 | |
| (dV/dt) _c * | (dI/dt) _c = 2.7A/ms | T _j =110°C | | TYP | 1 | 1 | 5 | 5 | V/μs |

* For either polarity of electrode A₂ voltage with reference to electrode A₁.

ORDERING INFORMATION

| Package | I _T (RMS) | V _{DRM} / V _{RRM} | Sensitivity Specification | | | |
|----------------------|----------------------|-------------------------------------|---------------------------|---|---|---|
| | A | V | T | D | S | A |
| BTA (Insulated) | 6 | 400 | X | X | X | X |
| | | 600 | X | X | X | X |
| | | 700 | X | X | X | X |
| BTB (Uninsulated) | | 400 | X | X | X | X |
| | | 600 | X | X | X | X |
| | | 700 | X | X | X | X |

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ($F=50\text{Hz}$).
(Curves are cut off by $(di/dt)_c$ limitation)

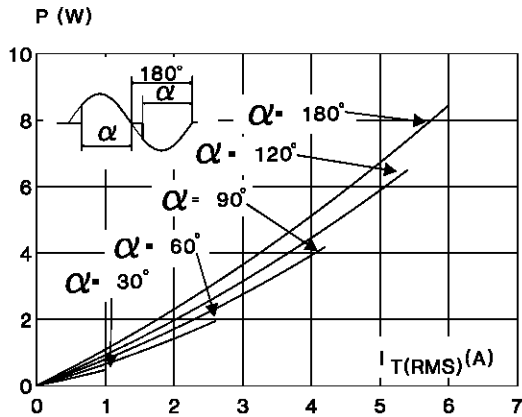


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

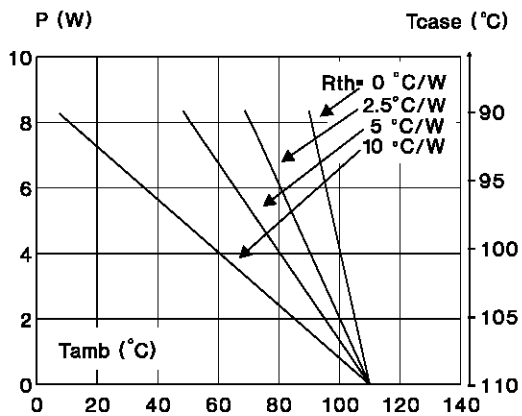


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

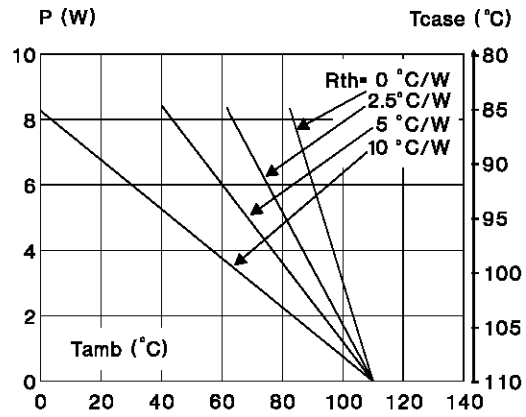


Fig.4 : RMS on-state current versus case temperature.

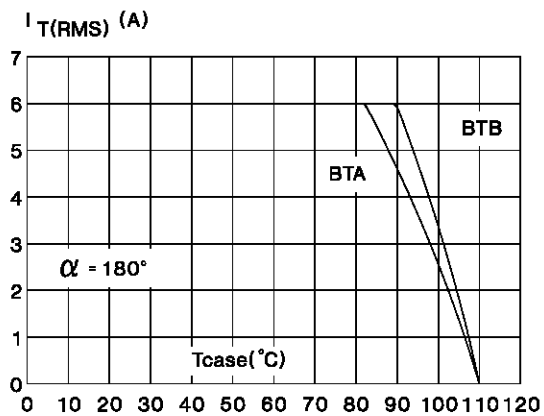


Fig.5 : Relative variation of thermal impedance versus pulse duration.

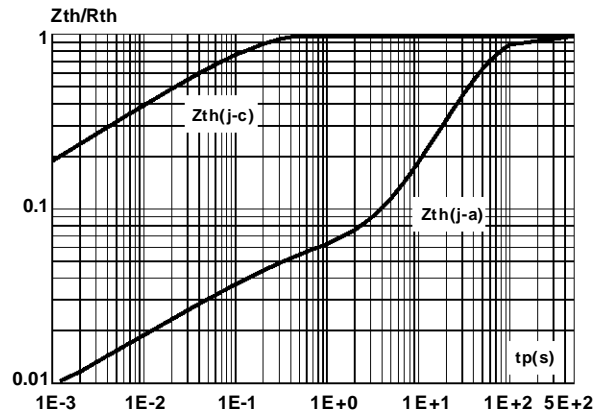


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

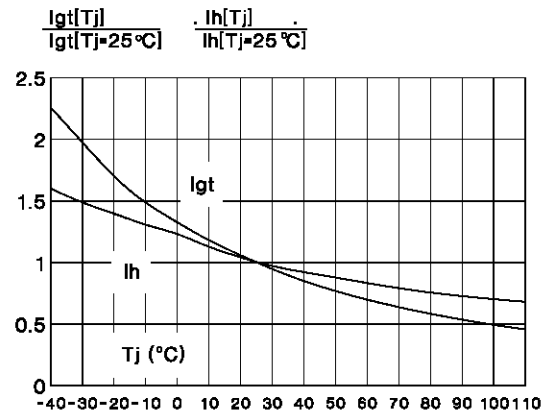


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

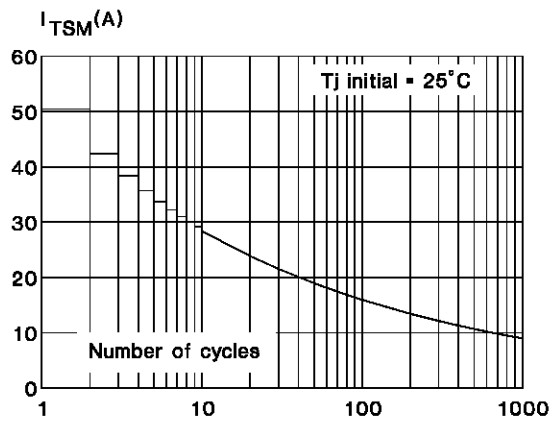


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10\text{ms}$, and corresponding value of I^2t .

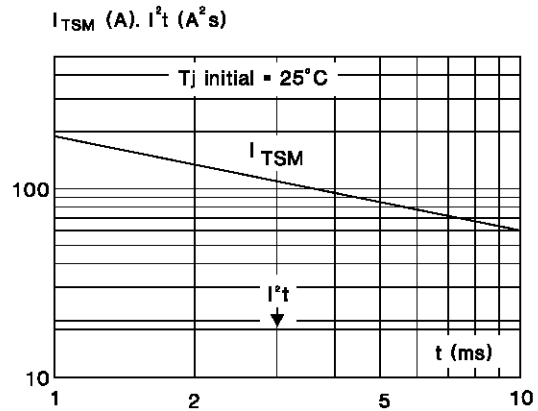
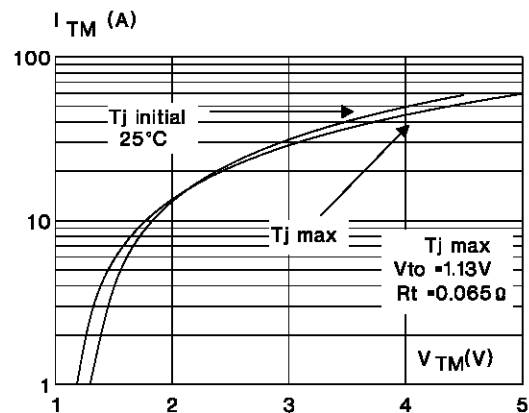
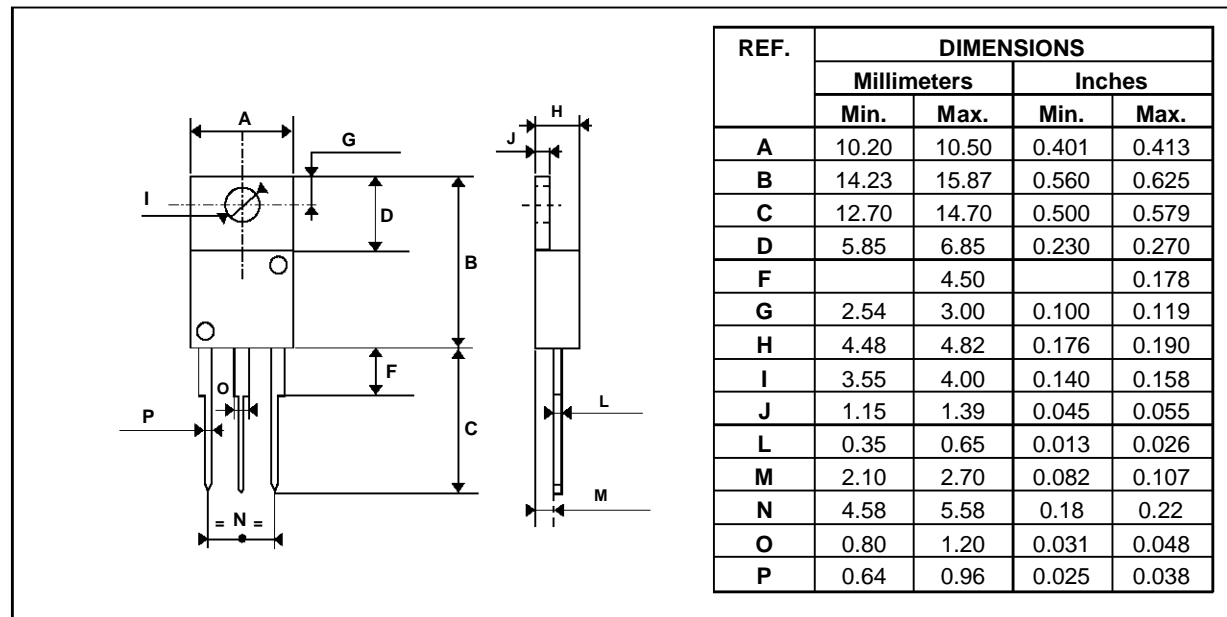


Fig.9 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

TO220AB Plastic



Cooling method : C

Marking : type number

Weight : 2.3 g

Recommended torque value : 0.8 m.N.

Maximum torque value : 1 m.N.

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